2SC5994

Bipolar Transistor 50V, 2A, Low VCE(sat), NPN Single



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Features

- Adoption of MBIT Process
- Low Collector to Emitter Saturation Voltage
- Large Current Capacity
- High Speed Switching

Typical Applications

- Voltage Regulators
- Relay Drivers
- Lamp Drivers
- Electrical Equipment

SPECIFICATIONS

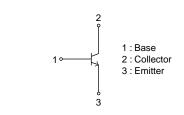
ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1, 2)

Parameter	Symbol	Value	Unit	
Collector to Base Voltage	VCBO	100	V	
Collector to Emitter Voltage	VCES	100	V	
Collector to Emitter Voltage	VCEO	50	V	
Emitter to Base Voltage	VEBO	6	V	
Collector Current	IC	2	Α	
Collector Current (Pulse)	ICP	4	Α	
Base Current	ΙΒ	400	mA	
Collector Dissipation	(Note 2)	Do	1.3	W
	Tc=25°C	PC	3.5	W
Junction Temperature	Tj	150	°C	
Storage Temperature	Tstg	-55 to +150	°C	

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Note 2 : Surface mounted on ceramic substrate(450mm² × 0.8mm)

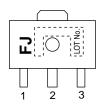
ELECTRICAL CONNECTION



MARKING



SOT-89 / PCP-1



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

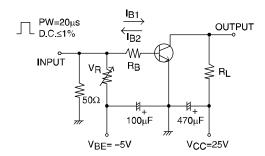
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ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 3)

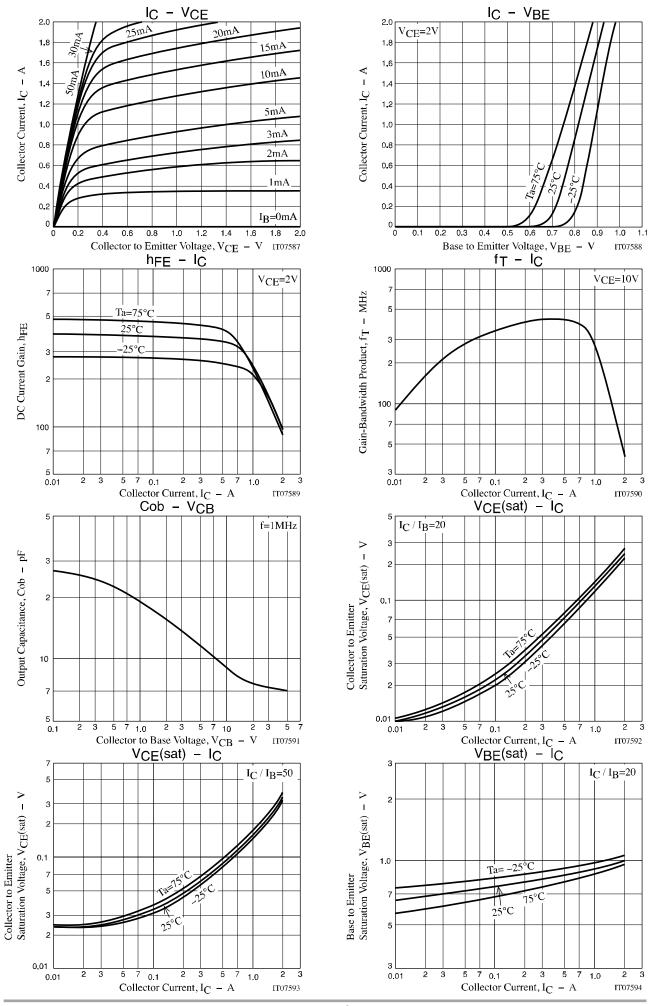
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Parameter	Symbol	Conditions	min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =50V, I _E =0A			1	μΑ
Emitter Cutoff Current	IEBO	VEB=4V, IC=0A			1	μΑ
DC Current Gain	hFE1	VCE=2V, IC=100mA	200		560	
	hFE2	V _{CE} =2V,I _C =1.5A	40			
Gain-Bandwidth Product	fT	VCE=10V, IC=300mA		420		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		9		pF
Collector to Emitter Saturation Voltage	V _{CE} (sat)	I _C =1A, I _B =50mA		135	300	mV
Base to Emitter Saturation Voltage	V _{BE} (sat)	IC=1A, IB=50mA		0.9	1.2	V
Collector to Base Breakdown Voltage	V(BR)CBO	I _C =10μΑ, I _E =0Α	100			V
Collector to Emitter Breakdown Voltage	V(BR)CES	IC=100μA, R _{BE} =0Ω	100			V
	V(BR)CEO	IC=1mA, RBE=∞	50			V
Emitter to Base Breakdown Voltage	V(BR)EBO	IE=10μA, IC=0A	6			V
Turn-On Time	ton			30		ns
Storage Time	t _{stg}	See specified Test Circuit		330	•	ns
Fall Time	tf	Gircuit		40		ns

Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

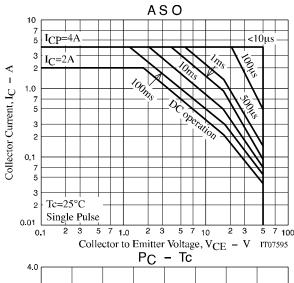
Switching Time Test Circuit

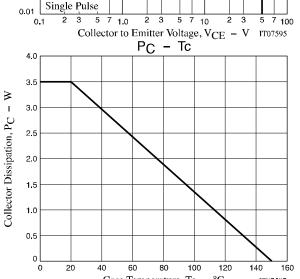


 $I_{C}=10I_{B1}=-10I_{B2}=700\text{mA}$



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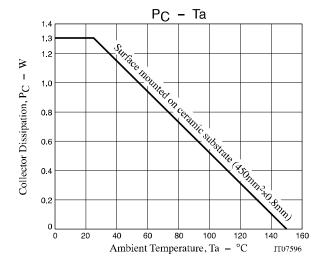


40 60 80 100 120 Case Temperature, Tc — °C

20

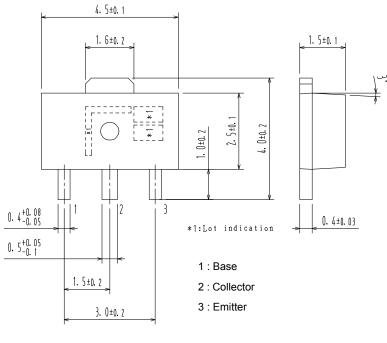
100

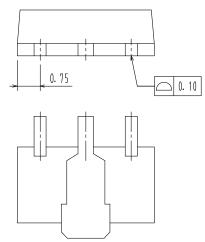
160 IT07597



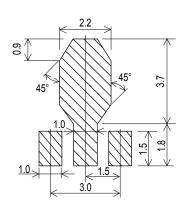
PACKAGE DIMENSIONS

unit: mm SOT-89 / PCP-1 CASE 419AU ISSUE O





Recommended Soldering Footprint



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)
2SC5994-TD-E FJ		SOT-89 / PCP-1 (Pb-Free)	1,000 / Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

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